



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(on)} Max	I _D Max T _C = +25°C	
-30V	10mΩ @ V _{GS} = -10V	-50A	
	18mΩ @ V _{GS} = -4.5V	-37A	

Features and Benefits

- Low R_{DS(on)} Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP3011SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

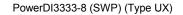
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

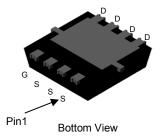
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

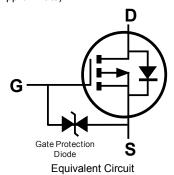






Top View





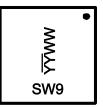
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3011SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMP3011SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SW9 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	±25	V		
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-19.8 -12	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-50 -40	А
Maximum Continuous Body Diode Forward Current (Note 7)			Is	-2.9	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-176	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-176	Α
Avalanche Current (Note 8) L = 1mH			las	-14	Α
Avalanche Energy (Note 8) L = 1mH			E _{AS}	104	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

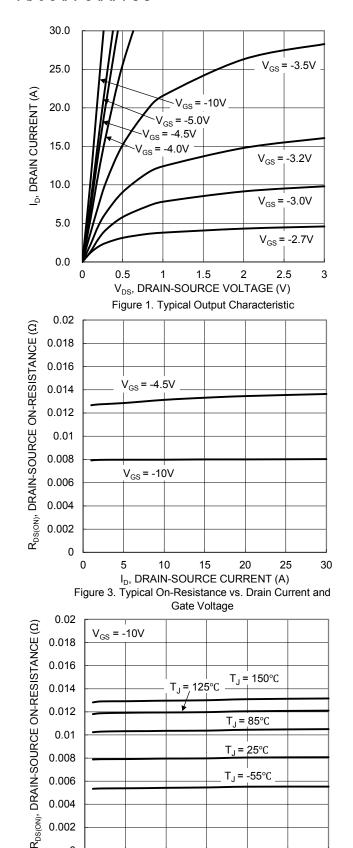
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	0.98	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	127	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.25	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	55	°C/W
Thermal Resistance, Junction to Case (Note 7)	Rejc	3.3	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(th)}	-1.0	_	-3.0	>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	D		8	10	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Dialii-Source Off-Resistance	R _{DS(on)}		13	18	11122	$V_{GS} = -4.5V$, $I_D = -8.5A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2380	_	pF	45)/)/ 0)/	
Output Capacitance	Coss	_	341	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$	
Reverse Transfer Capacitance	C _{rss}	_	296	_	pF	f = 1.0MHz	
Gate Resistance	R _g		3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V _{GS} = -5V)	Qq	_	25	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	46	_	nC), - 45\/ l - 44.5A	
Gate-Source Charge	Q _{gs}	_	6.8	_	nC	$V_{DS} = -15V, I_{D} = -11.5A$	
Gate-Drain Charge	Q_{gd}	_	13	_	nC	7	
Turn-On Delay Time	t _{D(on)}	_	6	_	ns		
Turn-On Rise Time	t _R	_	22	_	ns	V _{DD} = -15V, V _{GS} = -10V,	
Turn-Off Delay Time	t _{D(off)}	_	43	_	ns	$R_G = 6\Omega$, $I_D = -11.5A$	
Turn-Off Fall Time	t _F	_	33	_	ns	1	
Reverse Recovery Time	t _{RR}	_	19	_	ns	L = 44.5A di/dk = 400A/:	
Reverse Recovery Charge	Q_{RR}		8.9	_	nC	$I_S = -11.5A$, dl/dt = 100A/ μ s	

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.





I_D, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

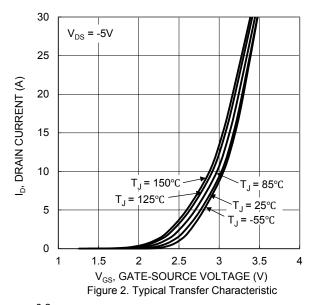
15

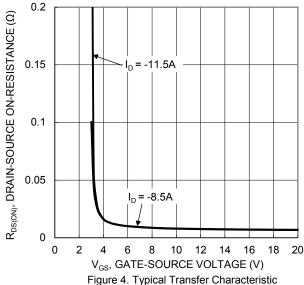
 $T_{.1} = -55^{\circ}C$

20

25

30





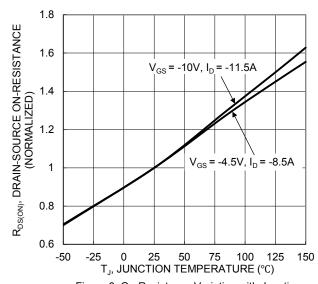


Figure 6. On-Resistance Variation with Junction Temperature

800.0

0.006 0.004

0.002

0

0

5

10



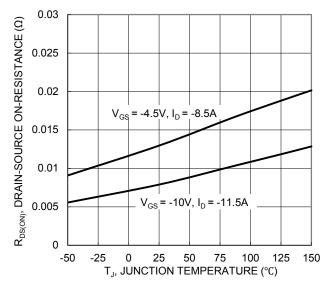
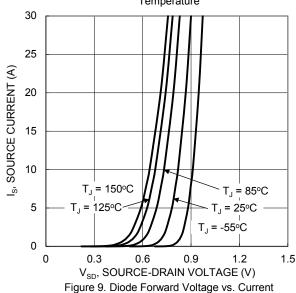


Figure 7. On-Resistance Variation with Junction Temperature



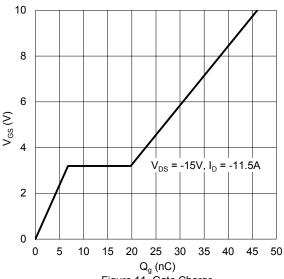


Figure 11. Gate Charge

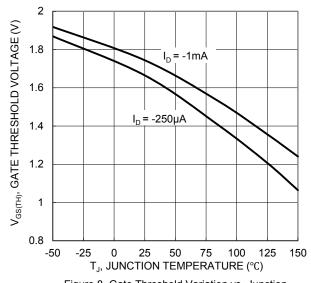
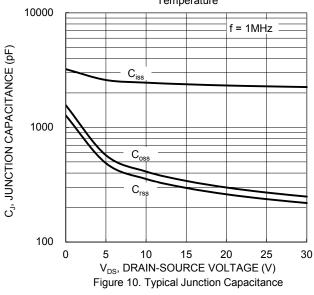
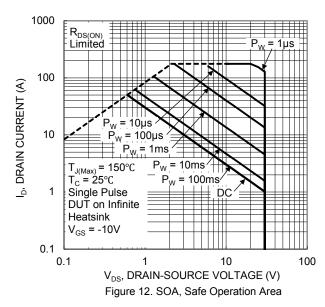


Figure 8. Gate Threshold Variation vs. Junction Temperature







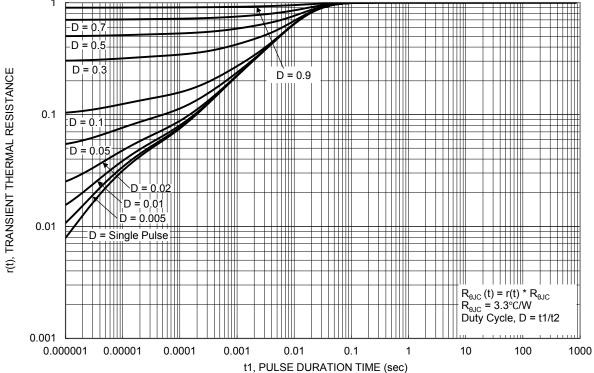


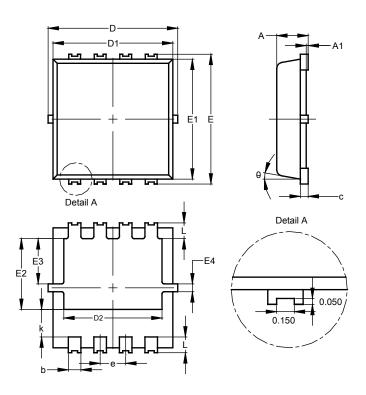
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

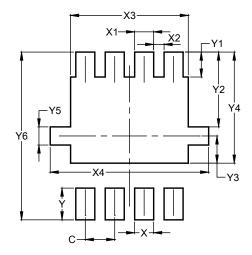


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	-	-	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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